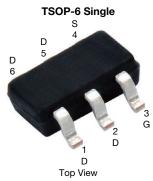
SQ3425CEV

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Vishay Siliconix

Automotive P-Channel 20 V (D-S) 175 °C MOSFET



Marking Code: 9P

PRODUCT SUMMARY				
V _{DS} (V)	-20			
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 V$	0.060			
$R_{DS(on)}$ (Ω) at V_{GS} = -2.5 V	0.100			
I _D (A)	-7.4			
Configuration	Single			

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



(1, 2, 5, 6) D (3) G (4) S

P-Channel MOSFET

ORDERING INFORMATION	
Package	TSOP-6
Lead (Pb)-free and halogen-free	SQ3425CEV (for detailed order number please see <u>www.vishay.com/doc?79771</u>)

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage	V _{DS}	-20	V		
Gate-source voltage		V _{GS}	± 12	v	
Continuous drain current	T _C = 25 °C	1-	-7.4		
Continuous drain current	T _C = 125 °C	ID	-4.3		
Continuous source current (diode conduction)	IS	-4.5	А		
Pulsed drain current ^a		I _{DM}	-29		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-11		
Single pulse avalanche energy		E _{AS}	6	mJ	
	T _C = 25 °C	P	5	W	
Maximum power dissipation	T _C = 125 °C	PD	1.67	VV V	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient	PCB mount ^b	R _{thJA}	110	°C/W		
Junction-to-foot (drain)		R _{thJF}	30	C/W		

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

b. When mounted on 1" square PCB (FR4 material)

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0, I_D = -250 \ \mu A$		-20	-	-	v
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	V _{DS} = V _{GS} , I _D = -250 μA		-1	-1.4	
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 12$ V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = -20 V	-	-	-1	μA
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -20 V, T _J = 125 °C	-	-	-50	
		$V_{GS} = 0 V$	V _{DS} = -20 V, T _J = 175 °C	-	-	-150	1
On-state drain current ^a	I _{D(on)}	V _{GS} = -4.5 V	$V_{DS} \le -5 V$	-15	-	-	Α
		V _{GS} = -4.5 V	I _D = -4.7 A	-	0.049	0.060	
	_	$V_{GS} = -4.5 V$	I _D = -4.7 A, T _J = 125 °C	-	0.065	-	Ω
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -4.5 V	I _D = -4.7 A, T _J = 175 °C	-	0.074	-	
		V _{GS} = -2.5 V	I _D = -1 A	-	0.089	0.100	
Forward transconductance ^a	g fs	V _{DS} =	-10 V, I _D = -4.7 A	-	9	-	S
Dynamic ^b	-					1	1
Input capacitance	C _{iss}		V _{DS} = -10 V, f = 1 MHz	-	564	840	pF
Output capacitance	Coss	$V_{GS} = 0 V$		-	162	267	
Reverse transfer capacitance	C _{rss}	-		-	120	190	
Total gate charge ^c	Q _q		V _{DS} = -10 V, I _D = -4.7 A	-	7.4	10.3	nC
Gate-source charge ^c	Q _{gs}	V _{GS} = -4.5 V		-	1.5	-	
Gate-drain charge ^c	Q _{gd}	-			2.7	-	-
Gate resistance	Rg		f = 1 MHz	3	6.3	9.1	Ω
Turn-on delay time ^c	t _{d(on)}				11	15	
Rise time ^c	t _r	- 	- 10 V, Rι = 10 Ω	-	26	35	1
Turn-off delay time ^c	t _{d(off)}		$V_{DD} = -10$ V, $R_L = 10 \Omega^2$ $I_D \cong -1$ A, $V_{GEN} = -4.5$ V, $R_g = 6 \Omega$		41	55	- ns
Fall time ^c	t _f	-			28	38	
Source-Drain Diode Ratings and Charac	teristics b						<u> </u>
Pulsed current ^a	I _{SM}			-	-	-21	Α
Forward voltage	V _{SD}	I _F = ·	I _F = -1.7 A, V _{GS} = 0 V		-0.8	-1.2	v
Body diode reverse recovery time	t _{rr}			-	18	36	ns
Body diode reverse recovery charge	Q _{rr}	1		-	8	16	nC
Reverse recovery fall time	ta	l _F = -1.5	A, di/dit = 100 A/µs	-	6	-	<u> </u>
Reverse recovery rise time	t _b	-		-	12	-	ns
Body diode peak reverse recovery current	I _{RM(REC)}			-	-0.86	_	A

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

b. Guaranteed by design, not subject to production testing

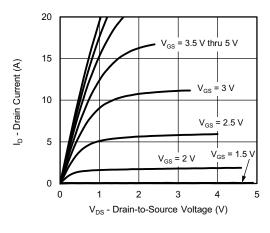
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

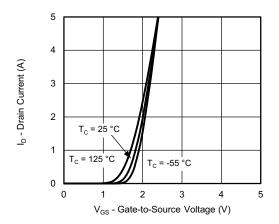


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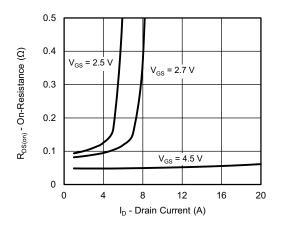
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



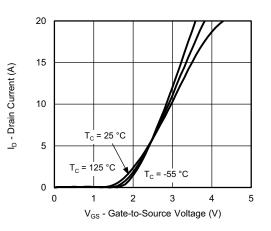
Output Characteristics



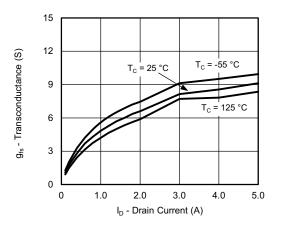
Transfer Characteristics



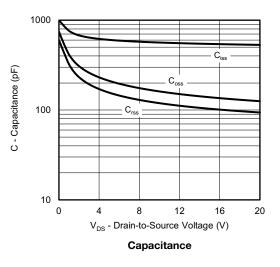
On-Resistance vs. Drain Current



Transfer Characteristics







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3

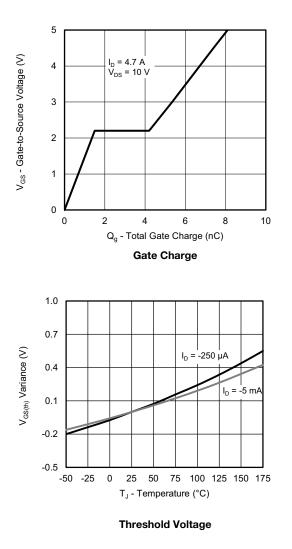
Document Number: 62373

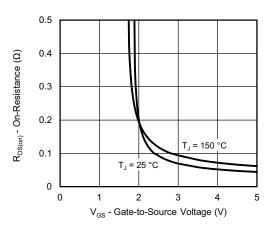
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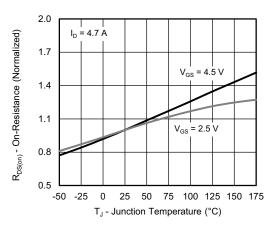
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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

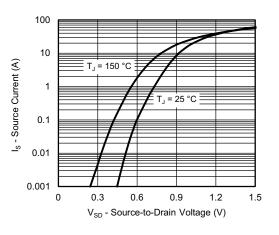




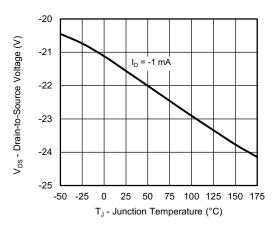




On-Resistance vs. Junction Temperature



Source Drain Diode Forward Voltage



Drain Source Breakdown vs. Junction Temperature

4

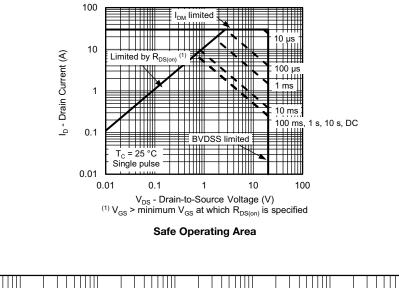
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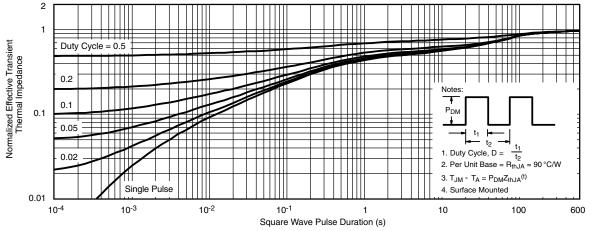


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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



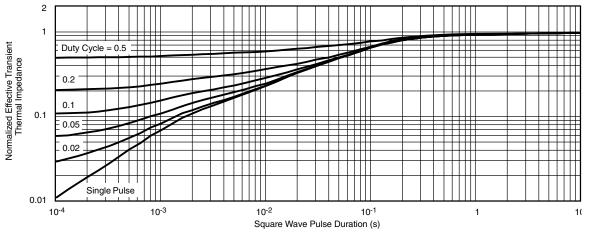


Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62373.



Package Information

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TSOP: 5/6-LEAD JEDEC Part Number: MO-193C









6-LEAD TSOP



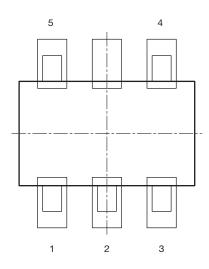
	MILLIMETERS			INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.91	-	1.10	0.036	-	0.043
A ₁	0.01	-	0.10	0.0004	-	0.004
A ₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
С	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
Е	2.70	2.85	2.98	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
е		0.95 BSC		0.0374 BSC		
e ₁	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L ₁		0.60 Ref			0.024 Ref	
L ₂	0.25 BSC				0.010 BSC	
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ_1	7° Nom				7° Nom	
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540						

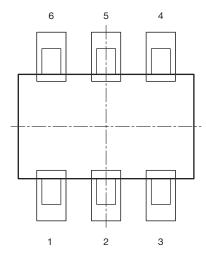
PAD Pattern



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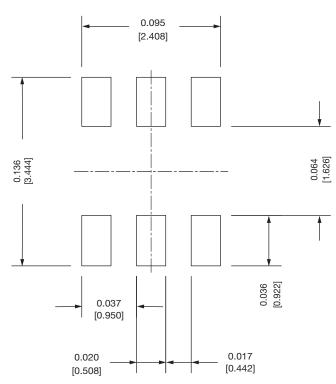
Recommended Land Pattern For TSOP-5L / TSOP-6L





TSOP 5L





Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022	
DWG: 3010	



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